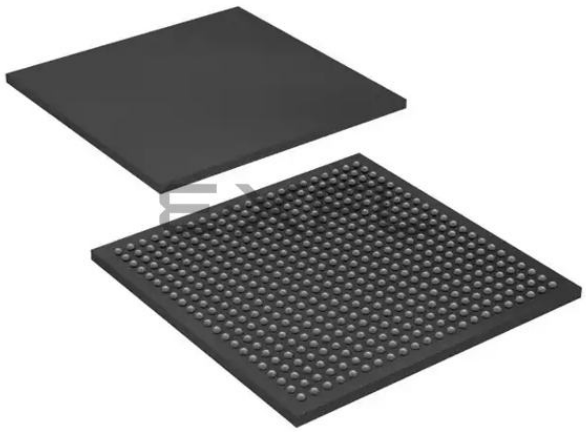


Welcome to E-XFL.COM

Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	360
Number of Logic Elements/Cells	2880
Total RAM Bits	40960
Number of I/O	220
Number of Gates	199000
Voltage - Supply	2.375V ~ 2.625V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	484-BBGA
Supplier Device Package	484-FBGA (23x23)
Purchase URL	https://www.e-xfl.com/product-detail/intel/epf10k50sfc484-3

Functional Description

Each FLEX 10KE device contains an enhanced embedded array to implement memory and specialized logic functions, and a logic array to implement general logic.

The embedded array consists of a series of EABs. When implementing memory functions, each EAB provides 4,096 bits, which can be used to create RAM, ROM, dual-port RAM, or first-in first-out (FIFO) functions. When implementing logic, each EAB can contribute 100 to 600 gates towards complex logic functions, such as multipliers, microcontrollers, state machines, and DSP functions. EABs can be used independently, or multiple EABs can be combined to implement larger functions.

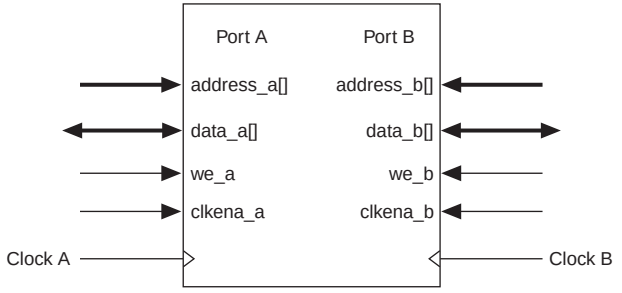
The logic array consists of logic array blocks (LABs). Each LAB contains eight LEs and a local interconnect. An LE consists of a four-input look-up table (LUT), a programmable flipflop, and dedicated signal paths for carry and cascade functions. The eight LEs can be used to create medium-sized blocks of logic—such as 8-bit counters, address decoders, or state machines—or combined across LABs to create larger logic blocks. Each LAB represents about 96 usable gates of logic.

Signal interconnections within FLEX 10KE devices (as well as to and from device pins) are provided by the FastTrack Interconnect routing structure, which is a series of fast, continuous row and column channels that run the entire length and width of the device.

Each I/O pin is fed by an I/O element (IOE) located at the end of each row and column of the FastTrack Interconnect routing structure. Each IOE contains a bidirectional I/O buffer and a flipflop that can be used as either an output or input register to feed input, output, or bidirectional signals. When used with a dedicated clock pin, these registers provide exceptional performance. As inputs, they provide setup times as low as 0.9 ns and hold times of 0 ns. As outputs, these registers provide clock-to-output times as low as 3.0 ns. IOEs provide a variety of features, such as JTAG BST support, slew-rate control, tri-state buffers, and open-drain outputs.

The EAB can also use Altera megafunctions to implement dual-port RAM applications where both ports can read or write, as shown in Figure 3.

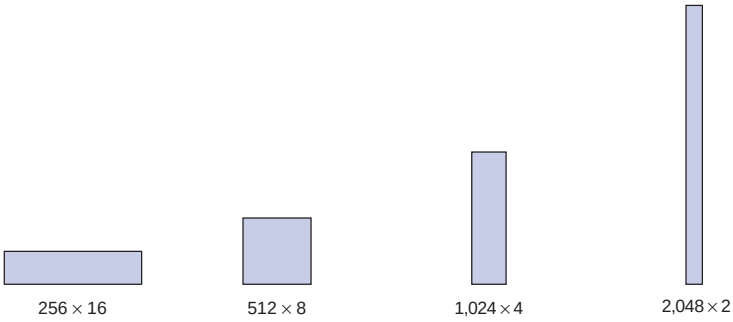
Figure 3. FLEX 10KE EAB in Dual-Port RAM Mode



The FLEX 10KE EAB can be used in a single-port mode, which is useful for backward-compatibility with FLEX 10K designs (see Figure 4).

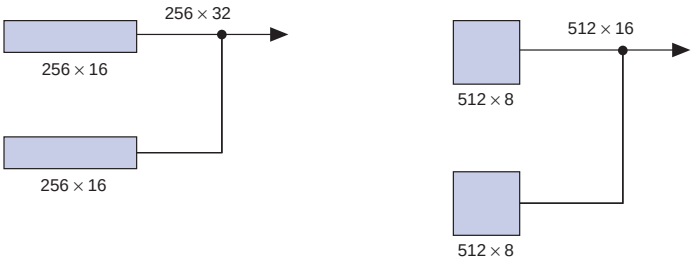
When used as RAM, each EAB can be configured in any of the following sizes: 256 × 16, 512 × 8, 1,024 × 4, or 2,048 × 2 (see Figure 5).

Figure 5. FLEX 10KE EAB Memory Configurations



Larger blocks of RAM are created by combining multiple EABs. For example, two 256 × 16 RAM blocks can be combined to form a 256 × 32 block; two 512 × 8 RAM blocks can be combined to form a 512 × 16 block (see Figure 6).

Figure 6. Examples of Combining FLEX 10KE EABs



If necessary, all EABs in a device can be cascaded to form a single RAM block. EABs can be cascaded to form RAM blocks of up to 2,048 words without impacting timing. The Altera software automatically combines EABs to meet a designer's RAM specifications.

The programmable flipflop in the LE can be configured for D, T, JK, or SR operation. The clock, clear, and preset control signals on the flipflop can be driven by global signals, general-purpose I/O pins, or any internal logic. For combinatorial functions, the flipflop is bypassed and the output of the LUT drives the output of the LE.

The LE has two outputs that drive the interconnect: one drives the local interconnect and the other drives either the row or column FastTrack Interconnect routing structure. The two outputs can be controlled independently. For example, the LUT can drive one output while the register drives the other output. This feature, called register packing, can improve LE utilization because the register and the LUT can be used for unrelated functions.

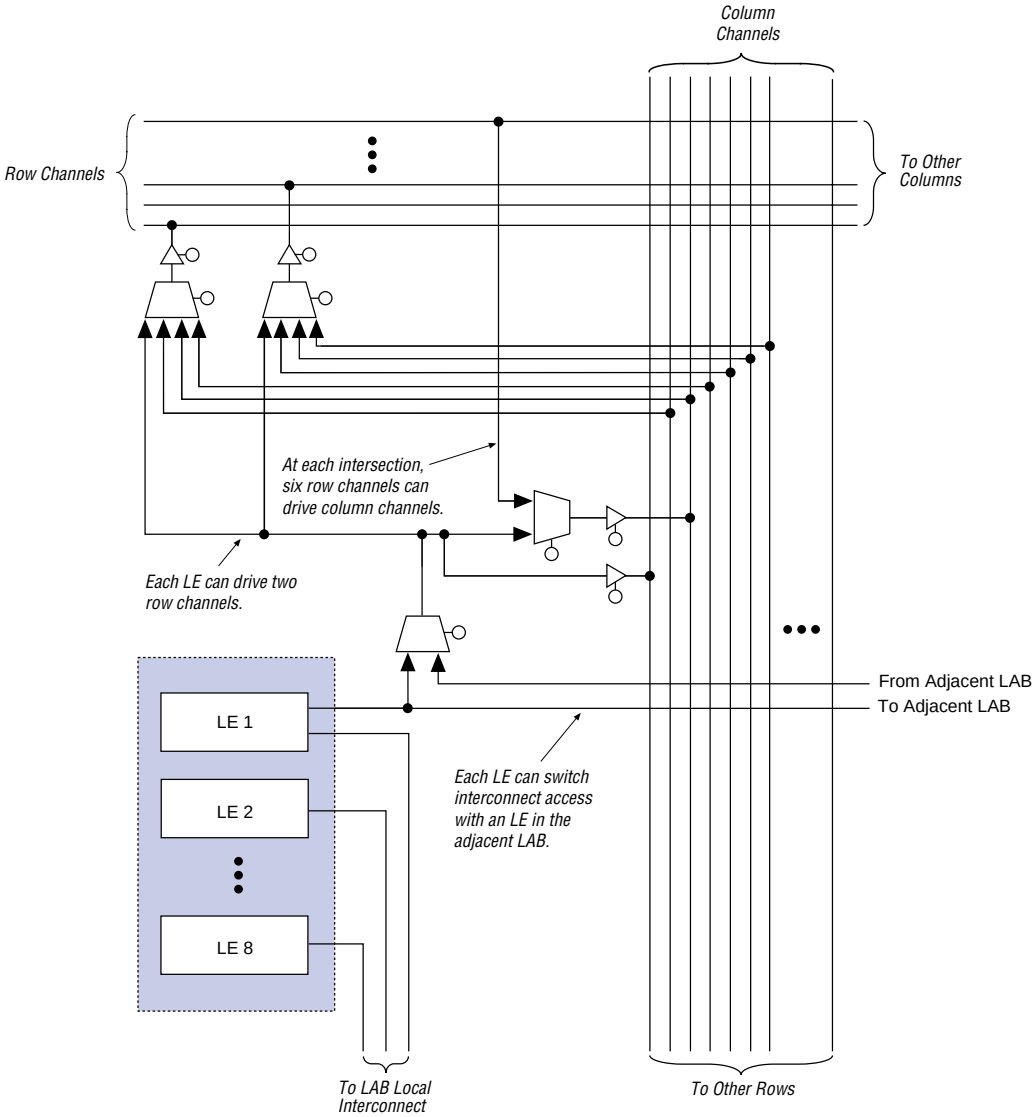
The FLEX 10KE architecture provides two types of dedicated high-speed data paths that connect adjacent LEs without using local interconnect paths: carry chains and cascade chains. The carry chain supports high-speed counters and adders and the cascade chain implements wide-input functions with minimum delay. Carry and cascade chains connect all LEs in a LAB as well as all LABs in the same row. Intensive use of carry and cascade chains can reduce routing flexibility. Therefore, the use of these chains should be limited to speed-critical portions of a design.

Carry Chain

The carry chain provides a very fast (as low as 0.2 ns) carry-forward function between LEs. The carry-in signal from a lower-order bit drives forward into the higher-order bit via the carry chain, and feeds into both the LUT and the next portion of the carry chain. This feature allows the FLEX 10KE architecture to implement high-speed counters, adders, and comparators of arbitrary width efficiently. Carry chain logic can be created automatically by the Altera Compiler during design processing, or manually by the designer during design entry. Parameterized functions such as LPM and DesignWare functions automatically take advantage of carry chains.

Carry chains longer than eight LEs are automatically implemented by linking LABs together. For enhanced fitting, a long carry chain skips alternate LABs in a row. A carry chain longer than one LAB skips either from even-numbered LAB to even-numbered LAB, or from odd-numbered LAB to odd-numbered LAB. For example, the last LE of the first LAB in a row carries to the first LE of the third LAB in the row. The carry chain does not cross the EAB at the middle of the row. For instance, in the EPF10K50E device, the carry chain stops at the eighteenth LAB and a new one begins at the nineteenth LAB.

Figure 13. FLEX 10KE LAB Connections to Row & Column Interconnect



On all FLEX 10KE devices (except EPF10K50E and EPF10K200E devices), the input path from the I/O pad to the FastTrack Interconnect has a programmable delay element that can be used to guarantee a zero hold time. EPF10K50S and EPF10K200S devices also support this feature. Depending on the placement of the IOE relative to what it is driving, the designer may choose to turn on the programmable delay to ensure a zero hold time or turn it off to minimize setup time. This feature is used to reduce setup time for complex pin-to-register paths (e.g., PCI designs).

Each IOE selects the clock, clear, clock enable, and output enable controls from a network of I/O control signals called the peripheral control bus. The peripheral control bus uses high-speed drivers to minimize signal skew across the device and provides up to 12 peripheral control signals that can be allocated as follows:

- Up to eight output enable signals
- Up to six clock enable signals
- Up to two clock signals
- Up to two clear signals

If more than six clock enable or eight output enable signals are required, each IOE on the device can be controlled by clock enable and output enable signals driven by specific LEs. In addition to the two clock signals available on the peripheral control bus, each IOE can use one of two dedicated clock pins. Each peripheral control signal can be driven by any of the dedicated input pins or the first LE of each LAB in a particular row. In addition, a LE in a different row can drive a column interconnect, which causes a row interconnect to drive the peripheral control signal. The chip-wide reset signal resets all IOE registers, overriding any other control signals.

When a dedicated clock pin drives IOE registers, it can be inverted for all IOEs in the device. All IOEs must use the same sense of the clock. For example, if any IOE uses the inverted clock, all IOEs must use the inverted clock and no IOE can use the non-inverted clock. However, LEs can still use the true or complement of the clock on a LAB-by-LAB basis.

The incoming signal may be inverted at the dedicated clock pin and will drive all IOEs. For the true and complement of a clock to be used to drive IOEs, drive it into both global clock pins. One global clock pin will supply the true, and the other will supply the complement.

When the true and complement of a dedicated input drives IOE clocks, two signals on the peripheral control bus are consumed, one for each sense of the clock.

When dedicated inputs drive non-inverted and inverted peripheral clears, clock enables, and output enables, two signals on the peripheral control bus will be used.

Tables 8 and 9 list the sources for each peripheral control signal, and show how the output enable, clock enable, clock, and clear signals share 12 peripheral control signals. The tables also show the rows that can drive global signals.

Table 8. Peripheral Bus Sources for EPF10K30E, EPF10K50E & EPF10K50S Devices

Peripheral Control Signal	EPF10K30E	EPF10K50E EPF10K50S
OE0	Row A	Row A
OE1	Row B	Row B
OE2	Row C	Row D
OE3	Row D	Row F
OE4	Row E	Row H
OE5	Row F	Row J
CLKENA0/CLK0/GLOBAL0	Row A	Row A
CLKENA1/OE6/GLOBAL1	Row B	Row C
CLKENA2/CLR0	Row C	Row E
CLKENA3/OE7/GLOBAL2	Row D	Row G
CLKENA4/CLR1	Row E	Row I
CLKENA5/CLK1/GLOBAL3	Row F	Row J

Column-to-IOE Connections

When an IOE is used as an input, it can drive up to two separate column channels. When an IOE is used as an output, the signal is driven by a multiplexer that selects a signal from the column channels. Two IOEs connect to each side of the column channels. Each IOE can be driven by column channels via a multiplexer. The set of column channels is different for each IOE (see Figure 17).

Figure 17. FLEX 10KE Column-to-IOE Connections

The values for m and n are provided in Table 11.

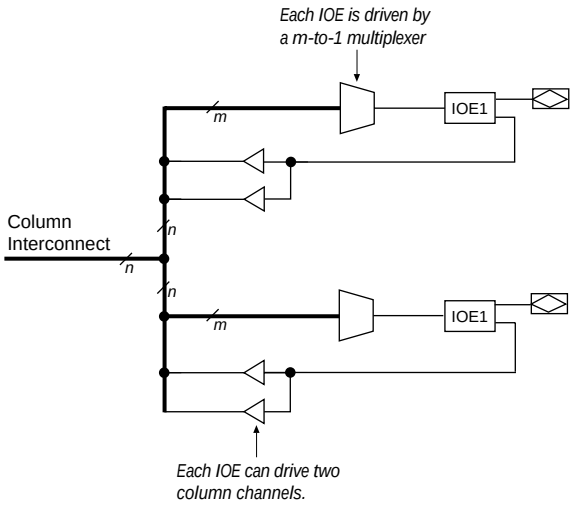


Table 11 lists the FLEX 10KE column-to-IOE interconnect resources.

Table 11. FLEX 10KE Column-to-IOE Interconnect Resources

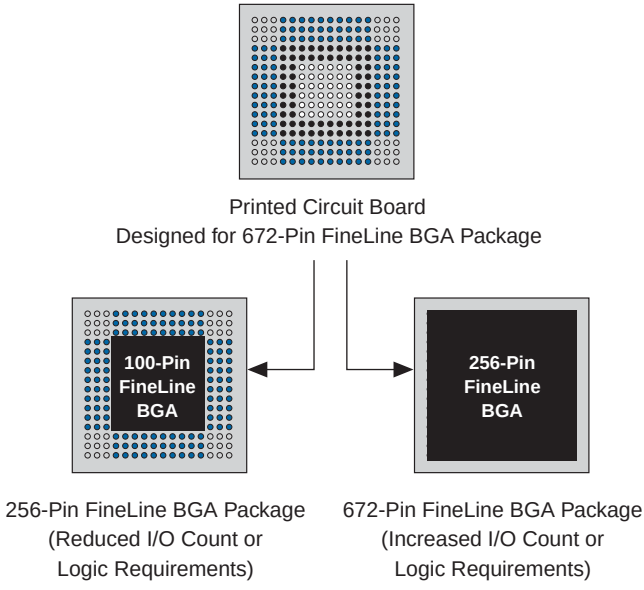
Device	Channels per Column *(n)*	Column Channels per Pin *(m)*
EPF10K30E	24	16
EPF10K50E EPF10K50S	24	16
EPF10K100E	24	16
EPF10K130E	32	24
EPF10K200E EPF10K200S	48	40

SameFrame Pin-Outs

FLEX 10KE devices support the SameFrame pin-out feature for FineLine BGA packages. The SameFrame pin-out feature is the arrangement of balls on FineLine BGA packages such that the lower-ball-count packages form a subset of the higher-ball-count packages. SameFrame pin-outs provide the flexibility to migrate not only from device to device within the same package, but also from one package to another. A given printed circuit board (PCB) layout can support multiple device density / package combinations. For example, a single board layout can support a range of devices from an EPF10K30E device in a 256-pin FineLine BGA package to an EPF10K200S device in a 672-pin FineLine BGA package.

The Altera software provides support to design PCBs with SameFrame pin-out devices. Devices can be defined for present and future use. The Altera software generates pin-outs describing how to lay out a board to take advantage of this migration (see Figure 18).

Figure 18. SameFrame Pin-Out Example



Tables 12 and 13 summarize the ClockLock and ClockBoost parameters for -1 and -2 speed-grade devices, respectively.

Table 12. ClockLock & ClockBoost Parameters for -1 Speed-Grade Devices

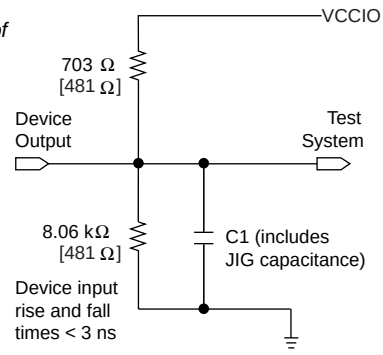
Symbol	Parameter	Condition	Min	Typ	Max	Unit
t_R	Input rise time				5	ns
t_F	Input fall time				5	ns
t_{INDUTY}	Input duty cycle		40		60	%
f_{CLK1}	Input clock frequency (ClockBoost clock multiplication factor equals 1)		25		180	MHz
f_{CLK2}	Input clock frequency (ClockBoost clock multiplication factor equals 2)		16		90	MHz
f_{CLKDEV}	Input deviation from user specification in the MAX+PLUS II software *(1)*				25,000 *(2)*	PPM
$t_{INCLKSTB}$	Input clock stability (measured between adjacent clocks)				100	ps
t_{LOCK}	Time required for ClockLock or ClockBoost to acquire lock *(3)*				10	µs
t_{JITTER}	Jitter on ClockLock or ClockBoost-generated clock *(4)*	$t_{INCLKSTB}$ < 100			250	ps
		$t_{INCLKSTB}$ < 50			200 *(4)*	ps
$t_{OUTDUTY}$	Duty cycle for ClockLock or ClockBoost-generated clock		40	50	60	%

Generic Testing

Each FLEX 10KE device is functionally tested. Complete testing of each configurable static random access memory (SRAM) bit and all logic functionality ensures 100% yield. AC test measurements for FLEX 10KE devices are made under conditions equivalent to those shown in Figure 21. Multiple test patterns can be used to configure devices during all stages of the production flow.

Figure 21. FLEX 10KE AC Test Conditions

Power supply transients can affect AC measurements. Simultaneous transitions of multiple outputs should be avoided for accurate measurement. Threshold tests must not be performed under AC conditions. Large-amplitude, fast-ground-current transients normally occur as the device outputs discharge the load capacitances. When these transients flow through the parasitic inductance between the device ground pin and the test system ground, significant reductions in observable noise immunity can result. Numbers in brackets are for 2.5-V devices or outputs. Numbers without brackets are for 3.3-V. devices or outputs.



Operating Conditions

Tables 19 through 23 provide information on absolute maximum ratings, recommended operating conditions, DC operating conditions, and capacitance for 2.5-V FLEX 10KE devices.

Table 19. FLEX 10KE 2.5-V Device Absolute Maximum Ratings *Note (1)*

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CCINT}	Supply voltage	With respect to ground *(2)*	–0.5	3.6	V
V_{CCIO}			–0.5	4.6	V
V_I	DC input voltage		–2.0	5.75	V
I_{OUT}	DC output current, per pin		–25	25	mA
T_{STG}	Storage temperature	No bias	–65	150	° C
T_{AMB}	Ambient temperature	Under bias	–65	135	° C
T_J	Junction temperature	PQFP, TQFP, BGA, and FineLine BGA packages, under bias		135	° C
		Ceramic PGA packages, under bias		150	° C

Table 24. LE Timing Microparameters (Part 2 of 2) *Note (1)*		
Symbol	**Parameter**	**Condition**
t_{CLR}	LE register clear delay	
t_{CH}	Minimum clock high time from clock pin	
t_{CL}	Minimum clock low time from clock pin	

Table 25. IOE Timing Microparameters *Note (1)*		
Symbol	**Parameter**	**Conditions**
t_{IOD}	IOE data delay	
t_{IOC}	IOE register control signal delay	
t_{IOCO}	IOE register clock-to-output delay	
t_{IOCOMB}	IOE combinatorial delay	
t_{IOSU}	IOE register setup time for data and enable signals before clock; IOE register recovery time after asynchronous clear	
t_{IOH}	IOE register hold time for data and enable signals after clock	
t_{IOCLR}	IOE register clear time	
t_{OD1}	Output buffer and pad delay, slow slew rate = off, V_{CCIO} = 3.3 V	C1 = 35 pF *(2)*
t_{OD2}	Output buffer and pad delay, slow slew rate = off, V_{CCIO} = 2.5 V	C1 = 35 pF *(3)*
t_{OD3}	Output buffer and pad delay, slow slew rate = on	C1 = 35 pF *(4)*
t_{XZ}	IOE output buffer disable delay	
t_{ZX1}	IOE output buffer enable delay, slow slew rate = off, V_{CCIO} = 3.3 V	C1 = 35 pF *(2)*
t_{ZX2}	IOE output buffer enable delay, slow slew rate = off, V_{CCIO} = 2.5 V	C1 = 35 pF *(3)*
t_{ZX3}	IOE output buffer enable delay, slow slew rate = on	C1 = 35 pF *(4)*
t_{INREG}	IOE input pad and buffer to IOE register delay	
t_{IOFD}	IOE register feedback delay	
t_{INCOMB}	IOE input pad and buffer to FastTrack Interconnect delay	

Table 26. EAB Timing Microparameters *Note (1)*

Symbol	Parameter	Conditions
$t_{EABDATA1}$	Data or address delay to EAB for combinatorial input	
$t_{EABDATA2}$	Data or address delay to EAB for registered input	
t_{EABWE1}	Write enable delay to EAB for combinatorial input	
t_{EABWE2}	Write enable delay to EAB for registered input	
t_{EABRE1}	Read enable delay to EAB for combinatorial input	
t_{EABRE2}	Read enable delay to EAB for registered input	
t_{EABCLK}	EAB register clock delay	
t_{EABCO}	EAB register clock-to-output delay	
$t_{EABBYPASS}$	Bypass register delay	
t_{EABSU}	EAB register setup time before clock	
t_{EABH}	EAB register hold time after clock	
t_{EABCLR}	EAB register asynchronous clear time to output delay	
t_{AA}	Address access delay (including the read enable to output delay)	
t_{WP}	Write pulse width	
t_{RP}	Read pulse width	
t_{WDSU}	Data setup time before falling edge of write pulse	*(5)*
t_{WDH}	Data hold time after falling edge of write pulse	*(5)*
t_{WASU}	Address setup time before rising edge of write pulse	*(5)*
t_{WAH}	Address hold time after falling edge of write pulse	*(5)*
t_{RASU}	Address setup time with respect to the falling edge of the read enable	
t_{RAH}	Address hold time with respect to the falling edge of the read enable	
t_{WO}	Write enable to data output valid delay	
t_{DD}	Data-in to data-out valid delay	
t_{EABOUT}	Data-out delay	
t_{EABCH}	Clock high time	
t_{EABCL}	Clock low time	

Table 33. EPF10K30E Device EAB Internal Microparameters *Note (1)*							
Symbol	**-1 Speed Grade**		**-2 Speed Grade**		**-3 Speed Grade**		**Unit**
	Min	**Max**	**Min**	**Max**	**Min**	**Max**	
$t_{EABDATA1}$		1.7		2.0		2.3	ns
$t_{EABDATA1}$		0.6		0.7		0.8	ns
t_{EABWE1}		1.1		1.3		1.4	ns
t_{EABWE2}		0.4		0.4		0.5	ns
t_{EABRE1}		0.8		0.9		1.0	ns
t_{EABRE2}		0.4		0.4		0.5	ns
t_{EABCLK}		0.0		0.0		0.0	ns
t_{EABCO}		0.3		0.3		0.4	ns
$t_{EABBYPASS}$		0.5		0.6		0.7	ns
t_{EABSU}	0.9		1.0		1.2		ns
t_{EABH}	0.4		0.4		0.5		ns
t_{EABCLR}	0.3		0.3		0.3		ns
t_{AA}		3.2		3.8		4.4	ns
t_{WP}	2.5		2.9		3.3		ns
t_{RP}	0.9		1.1		1.2		ns
t_{WDSU}	0.9		1.0		1.1		ns
t_{WDH}	0.1		0.1		0.1		ns
t_{WASU}	1.7		2.0		2.3		ns
t_{WAH}	1.8		2.1		2.4		ns
t_{RASU}	3.1		3.7		4.2		ns
t_{RAH}	0.2		0.2		0.2		ns
t_{WO}		2.5		2.9		3.3	ns
t_{DD}		2.5		2.9		3.3	ns
t_{EABOUT}		0.5		0.6		0.7	ns
t_{EABCH}	1.5		2.0		2.3		ns
t_{EABCL}	2.5		2.9		3.3		ns

Table 43. EPF10K50E External Timing Parameters *Notes (1), (2)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{DRR}		8.5		10.0		13.5	ns
t_{INSU}	2.7		3.2		4.3		ns
t_{INH}	0.0		0.0		0.0		ns
t_{OUTCO}	2.0	4.5	2.0	5.2	2.0	7.3	ns
t_{PCISU}	3.0		4.2		-		ns
t_{PCIH}	0.0		0.0		-		ns
t_{PCICO}	2.0	6.0	2.0	7.7	-	-	ns

Table 44. EPF10K50E External Bidirectional Timing Parameters *Notes (1), (2)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$	2.7		3.2		4.3		ns
$t_{INHBIDIR}$	0.0		0.0		0.0		ns
$t_{OUTCOBIDIR}$	2.0	4.5	2.0	5.2	2.0	7.3	ns
$t_{XZBIDIR}$		6.8		7.8		10.1	ns
$t_{ZXBIDIR}$		6.8		7.8		10.1	ns

Notes to tables:
(1) All timing parameters are described in Tables 24 through 30 in this data sheet.
(2) These parameters are specified by characterization.

Tables 45 through 51 show EPF10K100E device internal and external timing parameters.

Table 45. EPF10K100E Device LE Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{LUT}		0.7		1.0		1.5	ns
t_{CLUT}		0.5		0.7		0.9	ns
t_{RLUT}		0.6		0.8		1.1	ns
t_{PACKED}		0.3		0.4		0.5	ns
t_{EN}		0.2		0.3		0.3	ns
t_{CICO}		0.1		0.1		0.2	ns
t_{CGEN}		0.4		0.5		0.7	ns

Table 53. EPF10K130E Device IOE Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{OD3}		4.0		5.6		7.5	ns
t_{XZ}		2.8		4.1		5.5	ns
t_{ZX1}		2.8		4.1		5.5	ns
t_{ZX2}		2.8		4.1		5.5	ns
t_{ZX3}		4.0		5.6		7.5	ns
t_{INREG}		2.5		3.0		4.1	ns
t_{IOFD}		0.4		0.5		0.6	ns
t_{INCOMB}		0.4		0.5		0.6	ns

Table 54. EPF10K130E Device EAB Internal Microparameters *(Part 1 of 2)* *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{EABDATA1}$		1.5		2.0		2.6	ns
$t_{EABDATA2}$		0.0		0.0		0.0	ns
t_{EABWE1}		1.5		2.0		2.6	ns
t_{EABWE2}		0.3		0.4		0.5	ns
t_{EABRE1}		0.3		0.4		0.5	ns
t_{EABRE2}		0.0		0.0		0.0	ns
t_{EABCLK}		0.0		0.0		0.0	ns
t_{EABCO}		0.3		0.4		0.5	ns
$t_{EABBYPASS}$		0.1		0.1		0.2	ns
t_{EABSU}	0.8		1.0		1.4		ns
t_{EABH}	0.1		0.2		0.2		ns
t_{EABCLR}	0.3		0.4		0.5		ns
t_{AA}		4.0		5.0		6.6	ns
t_{WP}	2.7		3.5		4.7		ns
t_{RP}	1.0		1.3		1.7		ns
t_{WDSU}	1.0		1.3		1.7		ns
t_{WDH}	0.2		0.2		0.3		ns
t_{WASU}	1.6		2.1		2.8		ns
t_{WAH}	1.6		2.1		2.8		ns
t_{RASU}	3.0		3.9		5.2		ns
t_{RAH}	0.1		0.1		0.2		ns
t_{WO}		1.5		2.0		2.6	ns

Table 58. EPF10K130E External Bidirectional Timing Parameters Notes (1), (2)							
Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$ (3)	2.2		2.4		3.2		ns
$t_{INHBIDIR}$ (3)	0.0		0.0		0.0		ns
$t_{INSUBIDIR}$ (4)	2.8		3.0		–		ns
$t_{INHBIDIR}$ (4)	0.0		0.0		–		ns
$t_{OUTCOBIDIR}$ (3)	2.0	5.0	2.0	7.0	2.0	9.2	ns
$t_{XZBIDIR}$ (3)		5.6		8.1		10.8	ns
$t_{ZXBIDIR}$ (3)		5.6		8.1		10.8	ns
$t_{OUTCOBIDIR}$ (4)	0.5	4.0	0.5	6.0	–	–	ns
$t_{XZBIDIR}$ (4)		4.6		7.1		–	ns
$t_{ZXBIDIR}$ (4)		4.6		7.1		–	ns

Notes to tables:

(1) All timing parameters are described in Tables 24 through 30 in this data sheet.
(2) These parameters are specified by characterization.
(3) This parameter is measured without the use of the ClockLock or ClockBoost circuits.
(4) This parameter is measured with the use of the ClockLock or ClockBoost circuits.

Tables 59 through 65 show EPF10K200E device internal and external timing parameters.

Table 59. EPF10K200E Device LE Timing Microparameters (Part 1 of 2) Note (1)							
Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{LUT}		0.7		0.8		1.2	ns
t_{CLUT}		0.4		0.5		0.6	ns
t_{RLUT}		0.6		0.7		0.9	ns
t_{PACKED}		0.3		0.5		0.7	ns
t_{EN}		0.4		0.5		0.6	ns
t_{CICO}		0.2		0.2		0.3	ns
t_{CGEN}		0.4		0.4		0.6	ns
t_{CGENR}		0.2		0.2		0.3	ns
t_{CASC}		0.7		0.8		1.2	ns
t_{C}		0.5		0.6		0.8	ns
t_{CO}		0.5		0.6		0.8	ns
t_{COMB}		0.4		0.6		0.8	ns
t_{SU}	0.4		0.6		0.7		ns

Table 61. EPF10K200E Device EAB Internal Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{EABDATA1}$		2.0		2.4		3.2	ns
$t_{EABDATA1}$		0.4		0.5		0.6	ns
t_{EABWE1}		1.4		1.7		2.3	ns
t_{EABWE2}		0.0		0.0		0.0	ns
t_{EABRE1}		0		0		0	ns
t_{EABRE2}		0.4		0.5		0.6	ns
t_{EABCLK}		0.0		0.0		0.0	ns
t_{EABCO}		0.8		0.9		1.2	ns
$t_{EABBYPASS}$		0.0		0.1		0.1	ns
t_{EABSU}	0.9		1.1		1.5		ns
t_{EABH}	0.4		0.5		0.6		ns
t_{EABCLR}	0.8		0.9		1.2		ns
t_{AA}		3.1		3.7		4.9	ns
t_{WP}	3.3		4.0		5.3		ns
t_{RP}	0.9		1.1		1.5		ns
t_{WDSU}	0.9		1.1		1.5		ns
t_{WDH}	0.1		0.1		0.1		ns
t_{WASU}	1.3		1.6		2.1		ns
t_{WAH}	2.1		2.5		3.3		ns
t_{RASU}	2.2		2.6		3.5		ns
t_{RAH}	0.1		0.1		0.2		ns
t_{WO}		2.0		2.4		3.2	ns
t_{DD}		2.0		2.4		3.2	ns
t_{EABOUT}		0.0		0.1		0.1	ns
t_{EABCH}	1.5		2.0		2.5		ns
t_{EABCL}	3.3		4.0		5.3		ns

Table 62. EPF10K200E Device EAB Internal Timing Macroparameters (Part 1 of 2) *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{EABAA}		5.1		6.4		8.4	ns
$t_{EABRCOMB}$	5.1		6.4		8.4		ns
$t_{EABRCREG}$	4.8		5.7		7.6		ns
t_{EABWP}	3.3		4.0		5.3		ns

Table 62. EPF10K200E Device EAB Internal Timing Macroparameters (Part 2 of 2) *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{EABWCOMB}$	6.7		8.1		10.7		ns
$t_{EABWCREG}$	6.6		8.0		10.6		ns
t_{EABDD}		4.0		5.1		6.7	ns
$t_{EABDATACO}$		0.8		1.0		1.3	ns
$t_{EABDATASU}$	1.3		1.6		2.1		ns
$t_{EABDATAH}$	0.0		0.0		0.0		ns
$t_{EABWESU}$	0.9		1.1		1.5		ns
t_{EABWEH}	0.4		0.5		0.6		ns
$t_{EABWDSU}$	1.5		1.8		2.4		ns
t_{EABWDH}	0.0		0.0		0.0		ns
$t_{EABWASU}$	3.0		3.6		4.7		ns
t_{EABWAH}	0.4		0.5		0.7		ns
t_{EABWO}		3.4		4.4		5.8	ns

Table 63. EPF10K200E Device Interconnect Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{DIN2IOE}$		4.2		4.6		5.7	ns
t_{DIN2LE}		1.7		1.7		2.0	ns
$t_{DIN2DATA}$		1.9		2.1		3.0	ns
$t_{DCLK2IOE}$		2.5		2.9		4.0	ns
$t_{DCLK2LE}$		1.7		1.7		2.0	ns
$t_{SAMELAB}$		0.1		0.1		0.2	ns
$t_{SAMEROW}$		2.3		2.6		3.6	ns
$t_{SAMECOLUMN}$		2.5		2.7		4.1	ns
$t_{DIFFROW}$		4.8		5.3		7.7	ns
$t_{TWOROWS}$		7.1		7.9		11.3	ns
$t_{LEPERIPH}$		7.0		7.6		9.0	ns
$t_{LABCARRY}$		0.1		0.1		0.2	ns
$t_{LABCASC}$		0.9		1.0		1.4	ns

Table 66. EPF10K50S Device LE Timing Microparameters (Part 2 of 2) *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{CGENR}		0.1		0.1		0.1	ns
t_{CASC}		0.5		0.8		1.0	ns
t_{C}		0.5		0.6		0.8	ns
t_{CO}		0.6		0.6		0.7	ns
t_{COMB}		0.3		0.4		0.5	ns
t_{SU}	0.5		0.6		0.7		ns
t_{H}	0.5		0.6		0.8		ns
t_{PRE}		0.4		0.5		0.7	ns
t_{CLR}		0.8		1.0		1.2	ns
t_{CH}	2.0		2.5		3.0		ns
t_{CL}	2.0		2.5		3.0		ns

Table 67. EPF10K50S Device IOE Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{IOD}		1.3		1.3		1.9	ns
t_{IOC}		0.3		0.4		0.4	ns
t_{IOCO}		1.7		2.1		2.6	ns
t_{IOCOMB}		0.5		0.6		0.8	ns
t_{IOSU}	0.8		1.0		1.3		ns
t_{IOH}	0.4		0.5		0.6		ns
t_{IOCLR}		0.2		0.2		0.4	ns
t_{OD1}		1.2		1.2		1.9	ns
t_{OD2}		0.7		0.8		1.7	ns
t_{OD3}		2.7		3.0		4.3	ns
t_{XZ}		4.7		5.7		7.5	ns
t_{ZX1}		4.7		5.7		7.5	ns
t_{ZX2}		4.2		5.3		7.3	ns
t_{ZX3}		6.2		7.5		9.9	ns
t_{INREG}		3.5		4.2		5.6	ns
t_{IOFD}		1.1		1.3		1.8	ns
t_{INCOMB}		1.1		1.3		1.8	ns